



# 《风光欣》技术资料

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## 2SB772

PNP EPITAXIAL SILICON TRANSISTOR

### \*Features

High  $h_{FE}$ : 160~320

$V_{CE(sat)} = -0.5V(\text{Max.})$  ( $I_C = -500mA, I_B = -20mA$ )

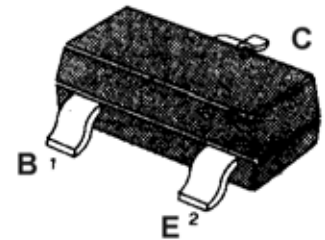
Low Collector Saturation Voltage

Complementary Pair With 2SD882

### ABSOLUTE MAXIMUM RATINGS( $T_A = 25$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-30	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-2	A
Collector Dissipation	$P_C$	225	mW
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~ 150	

SOT-23



### ELECTRICAL CHARACTERISTICS ( $T_A = 25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = -500 \mu A, I_E = 0$	-30			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = -1mA, I_B = 0$	-25			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = -50 \mu A, I_C = 0$	-5			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -20V, I_E = 0$			-500	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-500	nA
DC Current Gain	$h_{FE}$	$V_{CE} = 1V, I_C = -50mA$	160		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -20mA$			-0.5	V
Transition Frequency	$f_T$	$V_{CE} = -5V, I_C = -10mA$		120		MHz
Collector Output Capacitance	$C_{ob}$	$f = 1MHz, V_{CB} = -10V, I_E = 0$		13		pF

DEVICE MARKING : 2SB772 = B7